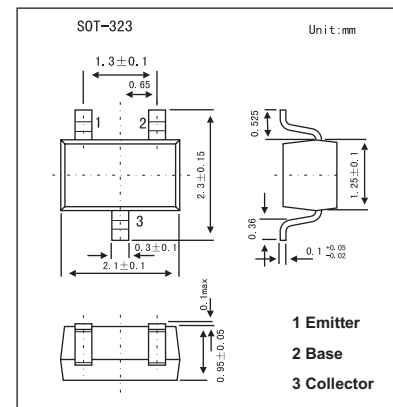


Silicon NPN Epitaxial Planar Type

2SD1824

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High emitter-base voltage V_{EBO}

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-emitter voltage	V_{CEO}	100	V
Emitter-base voltage	V_{EBO}	15	V
Peak collector current	I_{CP}	50	mA
Collector current	I_C	20	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	100			V
Collector-emitter voltage	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	100			V
Emitter-base voltage	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	15			V
Collector-base cutoff current	I_{CBO}	$V_{CB} = 60 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current	I_{CEO}	$V_{CE} = 60 \text{ V}, I_B = 0$			1	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	400		1200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.2	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		90		MHz

■ h_{FE} Classification

Marking	1V	
Rank	R	S
h_{FE}	400~800	600~1200